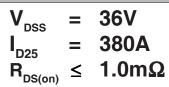


Advance Technical Information

TrenchT4[™] Power MOSFET

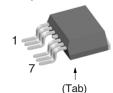
IXTA380N036T4-7



N-Channel Enhancement Mode Avalanche Rated

Symbol	Test Conditions	Maximum Ratings			
V _{DSS}	$T_{J} = 25^{\circ}C$ to $175^{\circ}C$	36	V		
V _{dgr}	$T_{_J}$ = 25°C to 175°C, $R_{_{GS}}$ = 1M Ω	36	V		
V _{GSM}	Transient	±15	V		
I _{D25}	$T_c = 25^{\circ}C$	380	А		
	Lead Current Limit, RMS	160	А		
I _{DM}	$\rm T_{\rm c}$ = 25°C, Pulse Width Limited by $\rm T_{\rm _{JM}}$	830	А		
I _A	$T_c = 25^{\circ}C$	190	A		
E _{AS}	$T_c = 25^{\circ}C$	1.4	J		
P _D	$T_c = 25^{\circ}C$	480	W		
T		-55 +175	°C		
T _{JM}		175	°C		
T _{stg}		-55 +175	°C		
T,	Maximum Lead Temperature for Soldering	g 300	0°		
	1.6 mm (0.062in.) from Case for 10s	260	°C		
F _c	Mounting Force	10.65 / 2.214.6	N/lb		
Weight		3.0	g		

TO-263 (7-lead)



Pins: 1 - Gate 2, 3, 5 , 6 , 7 - Source 4 (Tab) - Drain

Features

- International Standard Package
- 175°C Operating Temperature
- High Current Handling Capability
- Avalanche Rated
- Low R_{DS(on)}

Advantages

- · Easy to Mount
- Space Savings
- High Power Density

Applications

- DC-DC Converts & Off-Line UPS
- High Current Switching Applications
- Primary-Side Switch

Symbol (T _J = 25°C U	Test Conditions nless Otherwise Specified)	Chara Min.	acterist Typ.		
BV _{DSS}	$V_{gS} = 0V, I_{D} = 250 \mu A$	36			V
$V_{GS(th)}$	$V_{_{DS}} = V_{_{GS}}, I_{_{D}} = 250 \mu A$	2.0		4.0	V
I _{GSS}	$V_{gs} = \pm 15V, V_{ds} = 0V$			±200	nA
	$V_{\text{DS}} = V_{\text{DSS}}, V_{\text{GS}} = 0V$			10	μA
	T _J = 150°C			750	μA
R _{DS(on)}	$V_{_{GS}} = 10V, I_{_{D}} = 100A, Note 1$			1.0	mΩ

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IXTA380N036T4-7

SymbolTest ConditionsCharac $(T_J = 25^{\circ}C, Unless Otherwise Specified)Min.$		cteristic Typ.	Values Max.	
9 _{fs}	$V_{\rm DS} = 10V, I_{\rm D} = 60A, \text{ Note } 1$	05	175	S
R _{Gi}	Gate Input Resistance		1.0	Ω
C _{iss})		13.4	nF
C _{oss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		2400	pF
C _{rss})		1650	pF
t _{d(on)}	Posiotivo Switching Timos		36	ns
t,	Resistive Switching Times $V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		78	ns
t _{d(off)}	$\left(\begin{array}{c} \mathbf{v}_{\rm GS} = 10\mathbf{v}, \mathbf{v}_{\rm DS} = 0.0 \mathbf{v}_{\rm DSS}, \mathbf{v}_{\rm D} = 0.0 \mathbf{v}_{\rm D25} \\ \mathbf{R}_{\rm G} = 5\Omega \text{ (External)} \end{array}\right)$		125	ns
t _f) g · (· · · · · · · · · · · · · · · · ·		80	ns
Q _{g(on)}			260	nC
Q _{gs}	$V_{GS} = 10V, V_{DS} = 0.5 \bullet V_{DSS}, I_{D} = 0.5 \bullet I_{D25}$		60	nC
Q _{gd}	J		92	nC
R _{thJC}				0.31 °C/W

Source-Drain Diode

		Chara Min.	icteristio Typ.	c Values Max.	
I _s	$V_{gs} = 0V$			380	А
I _{SM}	Repetitive, Pulse width limited by $\mathrm{T}_{_{\mathrm{JM}}}$			1520	А
V _{SD}	$I_{_{\rm F}} = 100$ A, $V_{_{ m GS}} = 0$ V, Note 1			1.4	V
t _{rr}	$I_{\rm F} = 150 {\rm A}, V_{\rm GS} = 0 {\rm V}$		54		ns
I _{RM}	-di/dt = 100A/µs		2.6		Α
Q _{RM})	$V_{R} = 30V$		70		nC

Note 1: Pulse test, $t \le 300 \mu s$, duty cycle, $d \le 2\%$.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

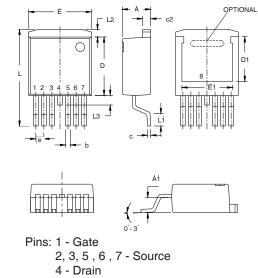
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
by one or more of the following U.S. patents	: 4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

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IXTA380N036T4-7

TO-263 (7-lead) (IXTA..7) Outline



SYM	INC	HES	MILLIMETER		
SIM	MIN	MAX	MIN	MAX	
А	.170	.185	4.30	4.70	
A 1	.085	.104	2.15	2.65	
b	.026	.035	0.65	0.90	
С	.016	.024	0.40	0.60	
с2	.049	.055	1.25	1.40	
D	.355	.370	9.00	9.40	
D 1	.272	.280	6.90	7,10	
Ε	.386	.402	9.80	10.20	
Ε1	.311	.319	7.90	8.10	
е	.050	BSC	1.27BSC		
L	.591	.614	15.00	15.60	
L1	.091	.110	2.30	2,80	
L2	.039	.059	1.00	1.50	
L3	.000	.059	0.00	1.50	



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单击下面可查看定价,库存,交付和生命周期等信息

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